

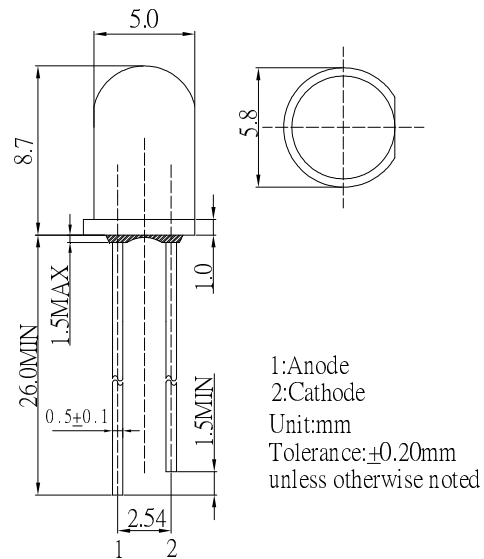
■Features

- Infrared Light Emitting Diode
- Package: 5mm clear epoxy
- UV Resistant Epoxy

■Applications

- IrDA
- Encoder
- Data Communication
- IR camera

■Outline Dimension



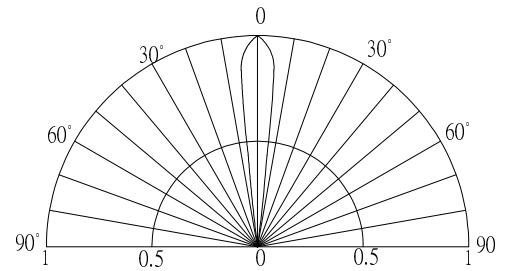
■Absolute Maximum Rating

(Ta=25°C)

Item	Symbol	Value	Unit
DC Forward Current	I _F	100	mA
Pulse Forward Current#	I _{FP}	200	mA
Reverse Voltage	V _R	5	V
Power Dissipation	P _D	190	mW
Operating Temperature	Topr	-30 ~ +85	°C
Storage Temperature	Tstg	-40~ +100	°C
Lead Soldering Temperature	Tsol	260°C/5sec	-

#Pulse width Max.10ms Duty ratio max 1/10

■Directivity



■Electrical -Optical Characteristics

(Ta=25°C)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
DC Forward Voltage*	V _F	I _F =100mA	-	1.6	1.8	V
DC Reverse Current	I _R	V _R =5V	-	-	10	μA
Peak Wavelength*	λ _p	I _F =100mA	866	880	892	nm
Radiant Intensity*	I _e	I _F =100mA	150	220	330	mW/Sr
Radiant Power*	P _O	I _F =100mA	50	60	-	mW
50% Power Angle	2θ _{1/2}	I _F =100mA	-	15	-	deg

*1 Tolerance of measurements of peak wavelength is ±1nm

*2 Tolerance of measurements of radiant power/intensity is ±15%

*3 Tolerance of measurements of forward voltage is ±0.1V